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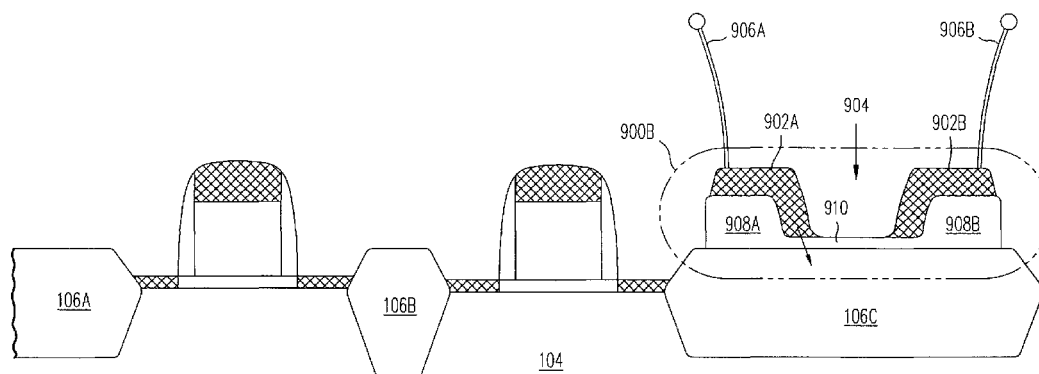
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(54) Title: CMOS PROCESS WITH AN INTEGRATED, HIGH PERFORMANCE, SILICIDE AGGLOMERATION FUSE



(57) Abstract: A complementary metal oxide semiconductor (CMOS) fabrication process. The process comprises creating a polysil-  
icon layer having a first thickness for a transistor gate area and a second thickness for a fuse area. The first thickness is greater than  
the second thickness, wherein most of the polysilicon in the fuse area will react with a metal layer to form polysilicide during a rapid  
thermal anneal (RTA) process.



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